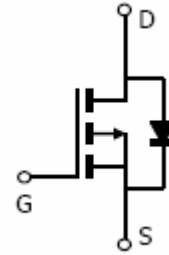


FNK P-Channel Enhancement Mode Power MOSFET

Description

The FNK3075PC/D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

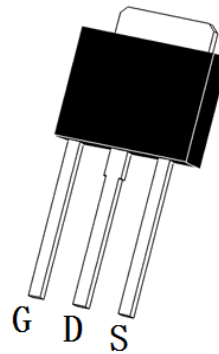


General Features

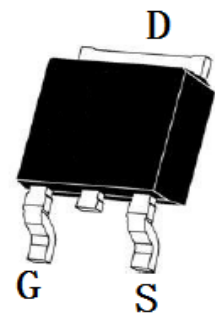
- $V_{DS} = -30V, I_D = -75A$
 $R_{DS(ON)} < 6.9m\Omega @ V_{GS} = -10V$
- High density cell design for ultra low $R_{ds(on)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Battery and loading switching



TO-251 top view



TO-252-2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
FNK3075PC	FNK3075PC	TO-251	-	-	-
FNK3075PD	FNK3075PD	TO-252	-	-	-

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-75	A
Pulsed Drain Current	I_{DM}	-300	A
Maximum Power Dissipation	P_D	35	W
Derating factor		0.28	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	368	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	3.6	°C/W
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Electrical Characteristics (TC=25°C unless otherwise noted)

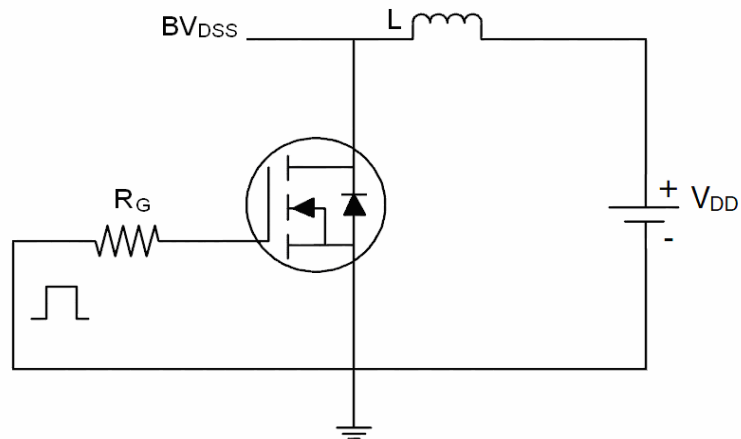
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-10A$	-	5	6.9	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-15A$	-	20	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	6105	-	PF
Output Capacitance	C_{oss}		-	785	-	PF
Reverse Transfer Capacitance	C_{rss}		-	600	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-10A$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	13	-	nS
Turn-on Rise Time	t_r		-	12	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	t_f		-	14	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-10A,$ $V_{GS}=-10V$	-	84	-	nC
Gate-Source Charge	Q_{gs}		-	11.7	-	nC
Gate-Drain Charge	Q_{gd}		-	25	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-10A$	-	-0.85	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-50	A
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -10A$	-	-	45	nS
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A/\mu s$ (Note3)	-	-	43	nC

Notes:

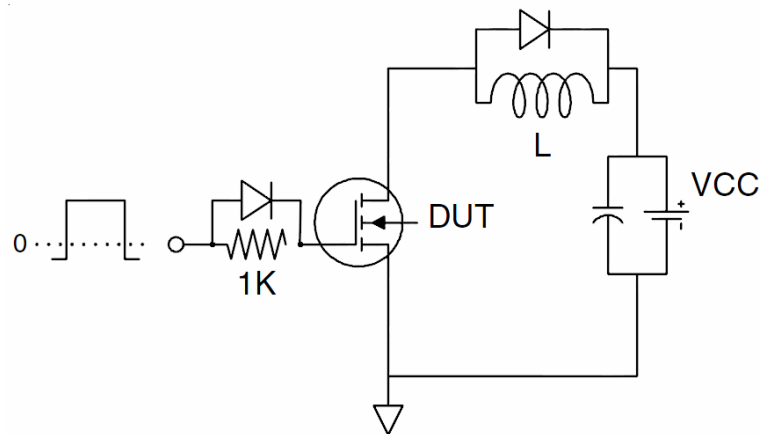
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition: $T_J=25^\circ C, V_{DB}=-15V, V_G=-10V, L=0.5mH, R_g=25\Omega$

Test Circuit

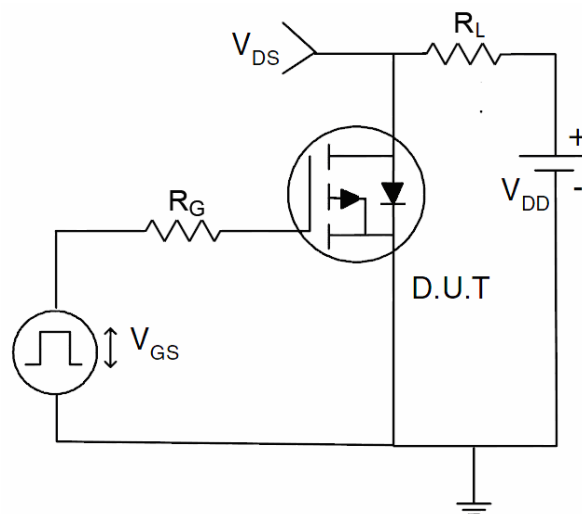
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

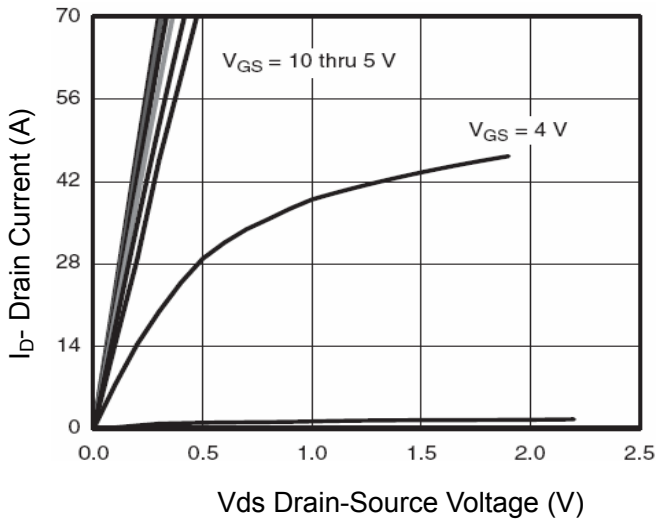


Figure 1 Output Characteristics

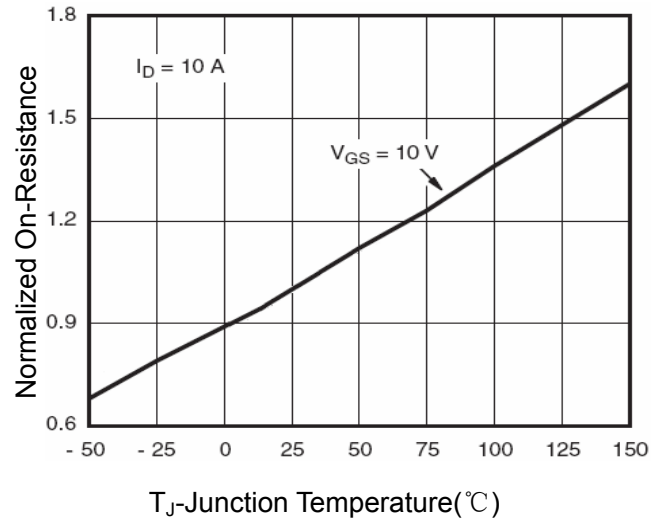


Figure 4 R_{dson} -Junction Temperature

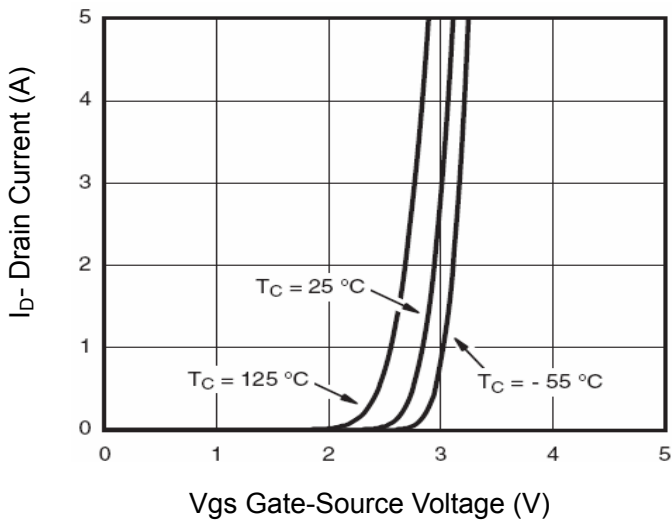


Figure 2 Transfer Characteristics

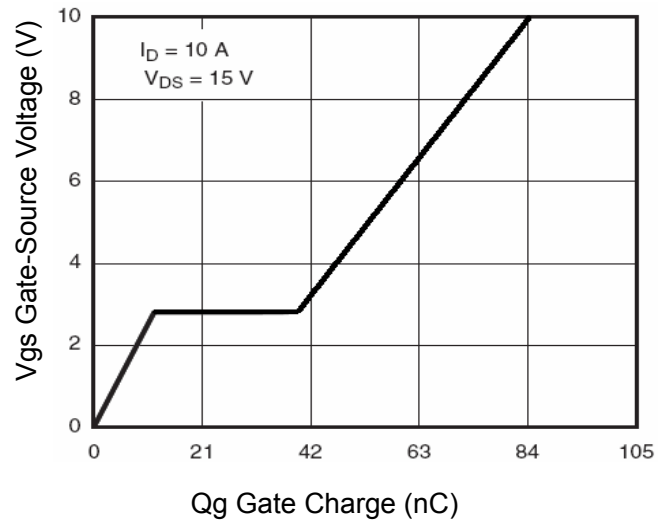


Figure 5 Gate Charge

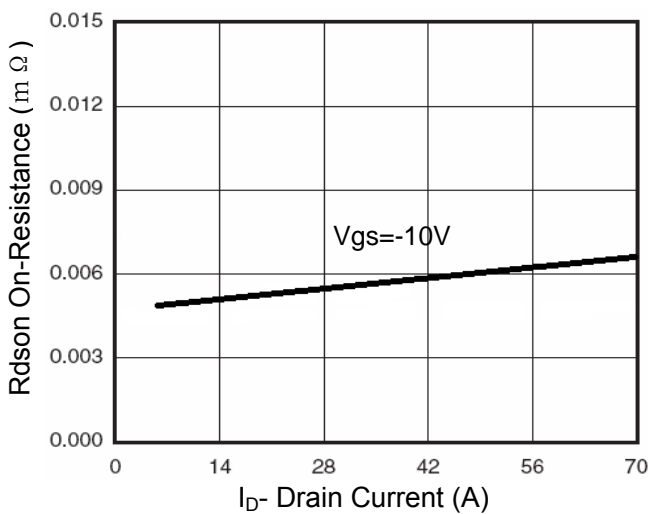


Figure 3 R_{dson} - Drain Current

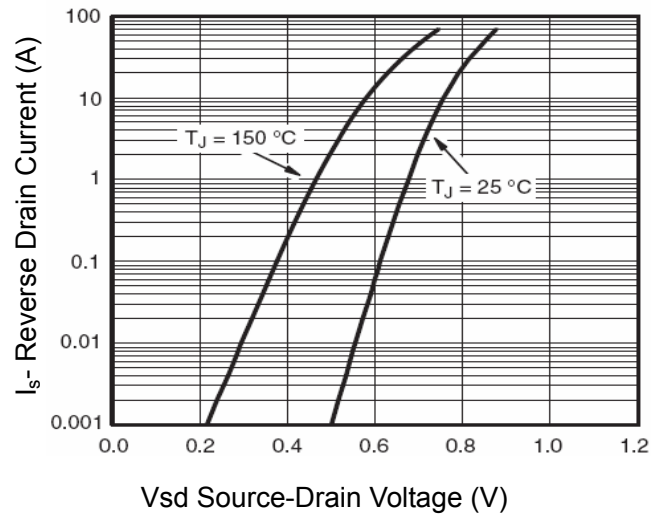


Figure 6 Source- Drain Diode Forward

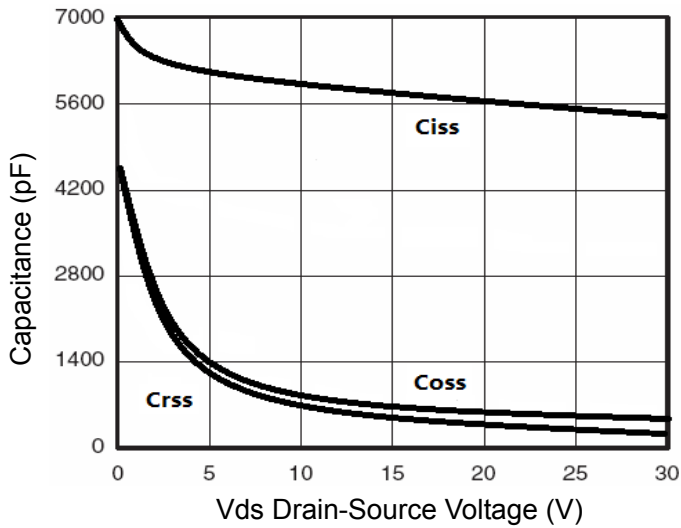


Figure 7 Capacitance vs Vds

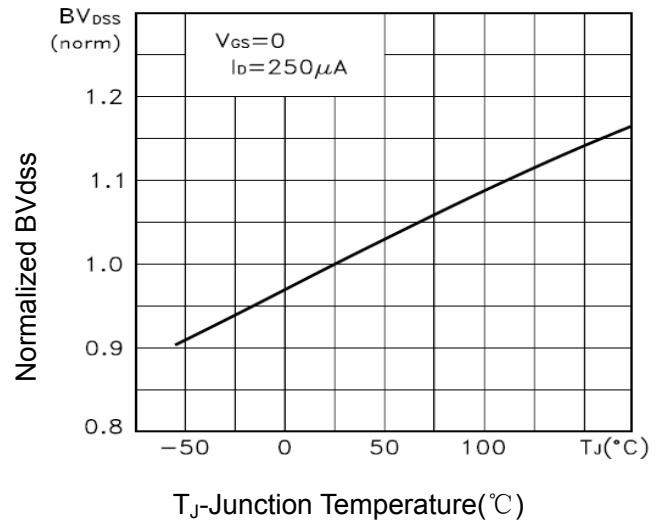


Figure 9 BV_{DSS} vs Junction Temperature

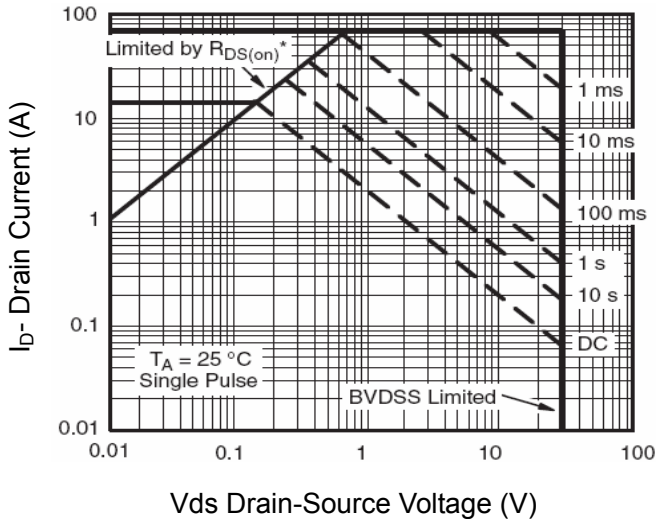


Figure 8 Safe Operation Area

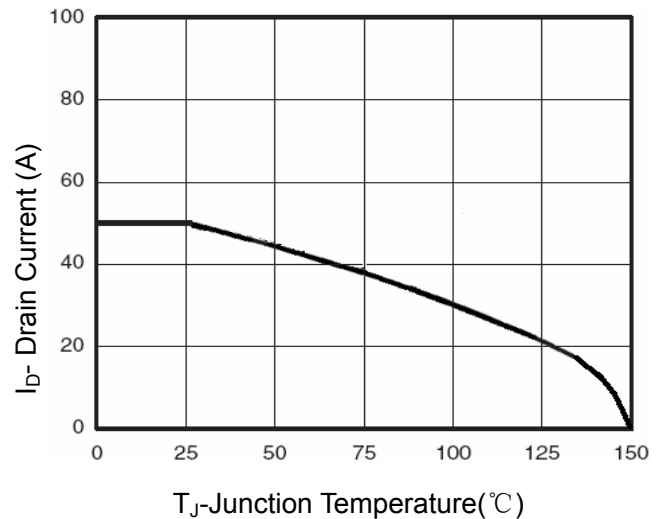


Figure 10 I_D Current Derating vs Junction Temperature

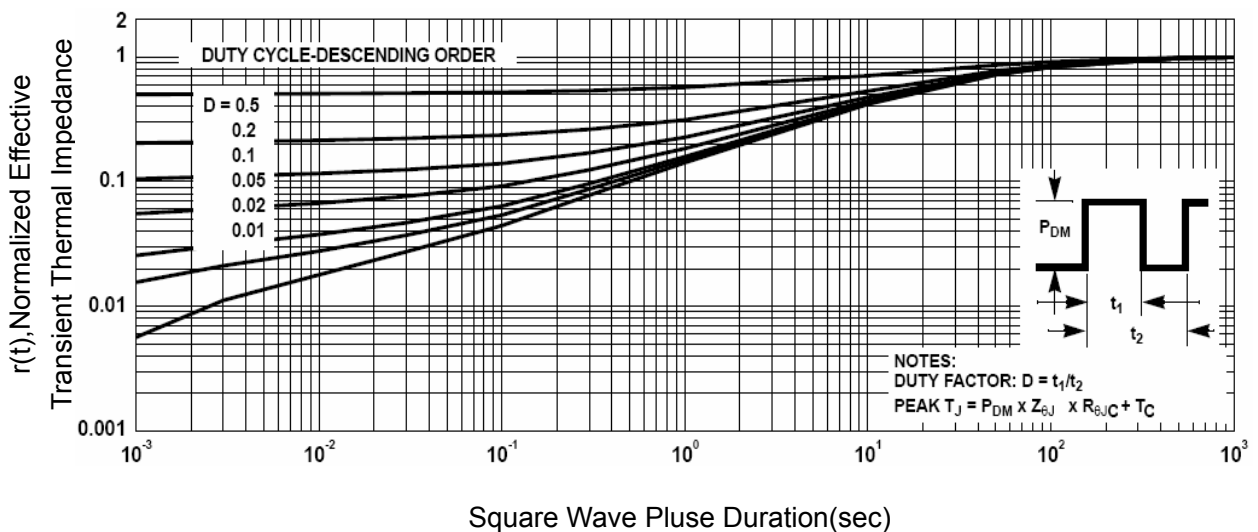
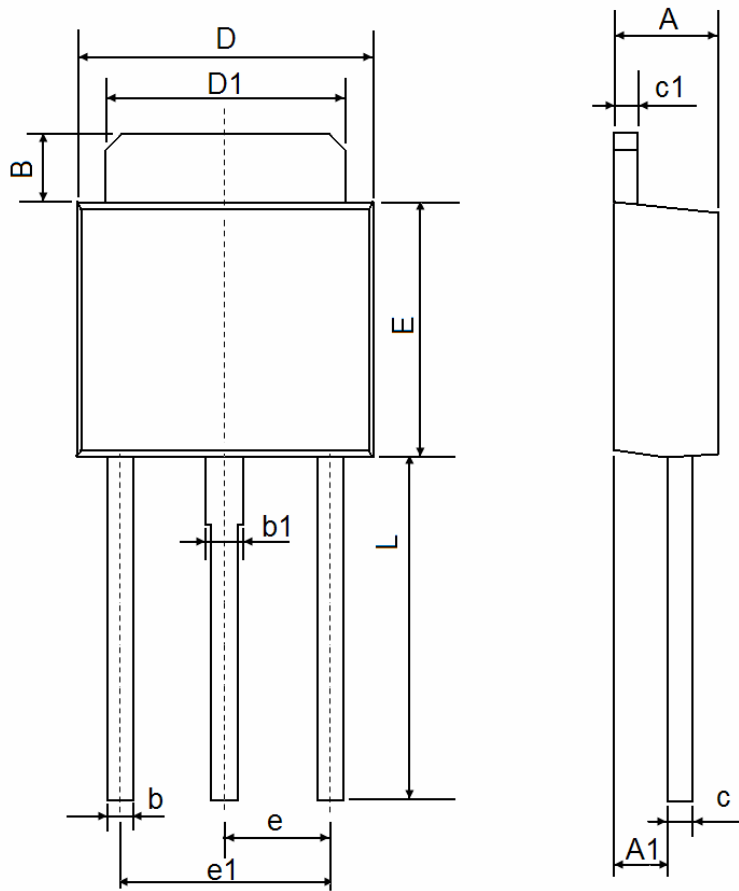


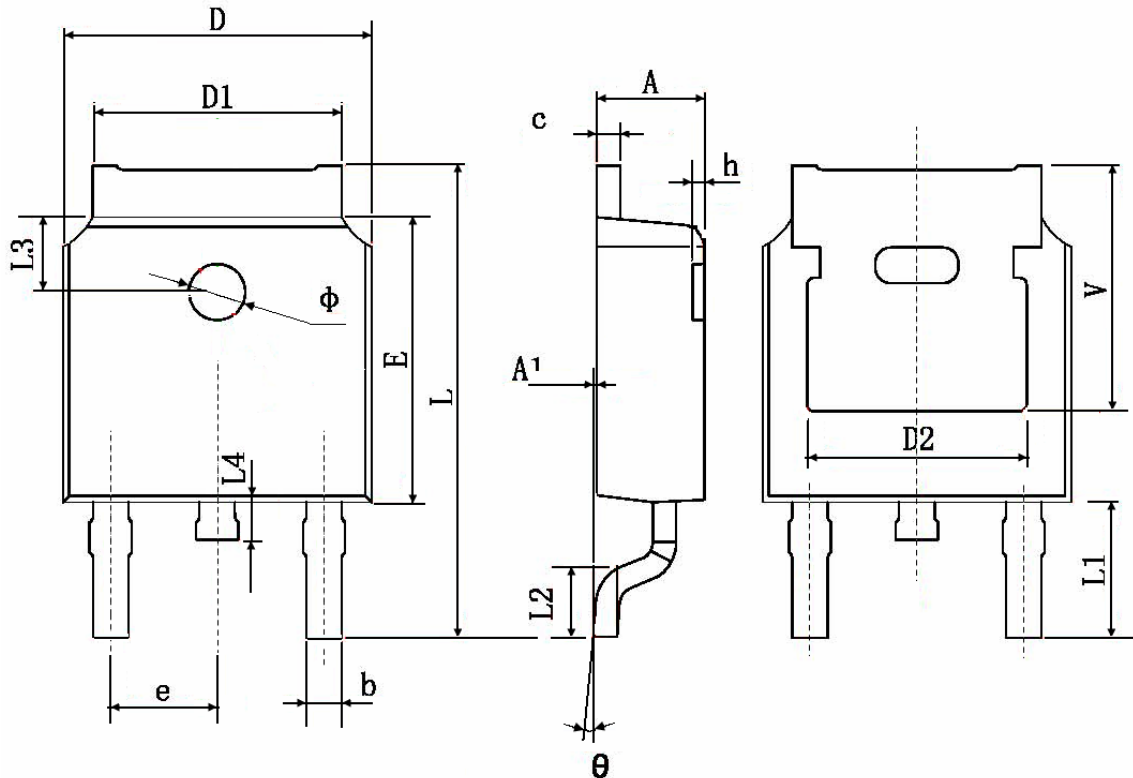
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-251 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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- FNK will supply the best possible product for customers!